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Vishay Siliconix

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^d Q _g (TYP		
100	0.0040 at V _{GS} = 10 V	120	76	
100	0.0046 at V _{GS} = 7.5 V	120	70	



Ordering Information:

SUP70040E-GE3 (Lead (Pb)-free and halogen-free)

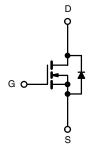
FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

- Power supply
 - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20	v		
Out 1	T _C = 25 °C	,	120 ^d		
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	I _D	120 ^d		
Pulsed Drain Current (t = 100 μs)	I _{DM}	480	A		
Avalanche Current		I _{AS}	73		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	266	mJ	
Maximum Dawar Dissipation 8	T _C = 25 °C	В	375 b	10/	
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{th,IC}	0.4]		

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Package limited.



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5	-	4		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	_	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	- μA	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	Α	
Dunin Course On Chata Basistana 3	0	V _{GS} = 10 V, I _D = 20 A	-	0.0032		0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 15 A	-	0.0035	0.0046	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	-	82	-	S	
Dynamic ^b				1			
Input Capacitance	C _{iss}		-	5100	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	2025	-		
Reverse Transfer Capacitance	C _{rss}		-	165	-		
Total Gate Charge ^c	Qg		-	76	120		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	23	-	nC	
Gate-Drain Charge ^c	Q_{gd}		-	17	-	1	
Gate Resistance	R_g	f = 1 MHz	0.6	3.3	6.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	30		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	22	40		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	55	100	ns	
Fall Time °	t _f		-	15	30		
Drain-Source Body Diode Ratings ar	d Characteri	stics ^b (T _C = 25 °C)		•			
Pulsed Current	I _{SM}		-	-	480	Α	
Forward Voltage ^a	V_{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V	

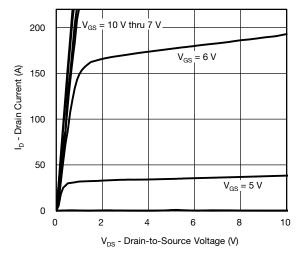
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

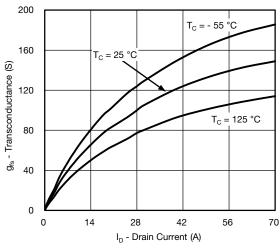
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



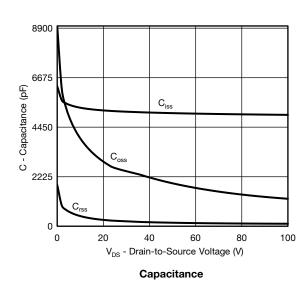
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

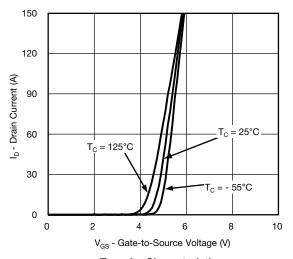


Output Characteristics

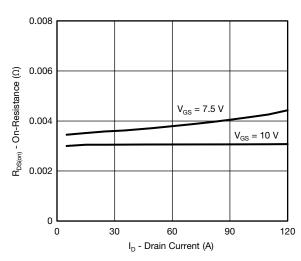


Transconductance

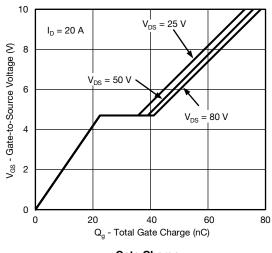




Transfer Characteristics

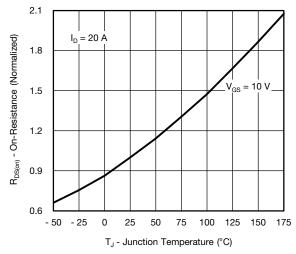


On-Resistance vs. Drain Current

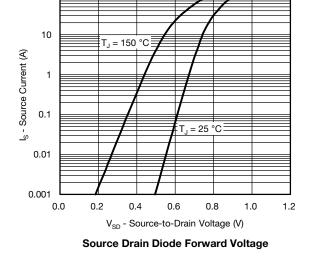




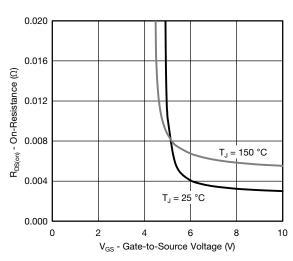
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



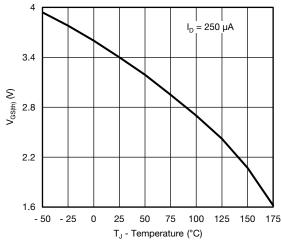
On-Resistance vs. Junction Temperature



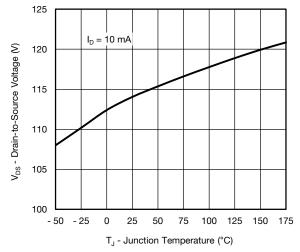
100



On-Resistance vs. Gate-to-Source Voltage



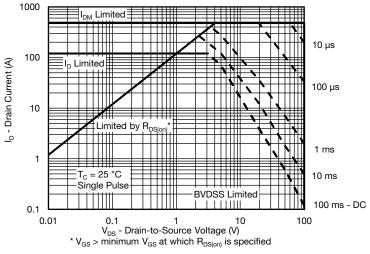
Threshold Voltage



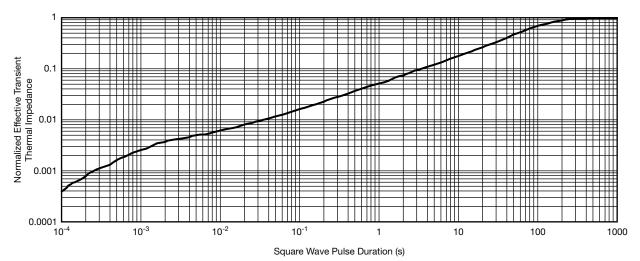
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



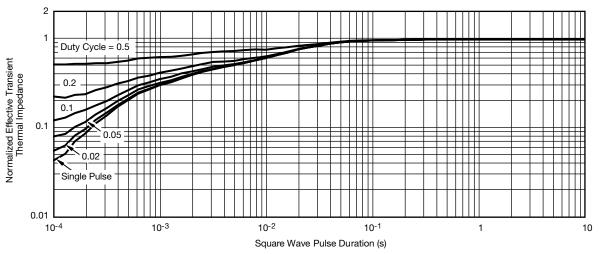
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

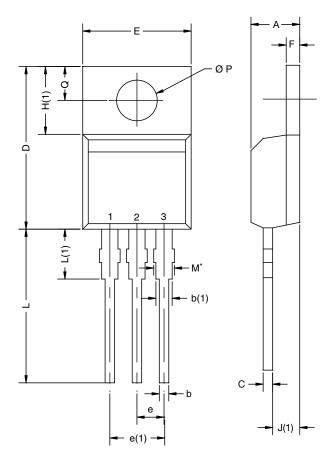
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62996.



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TO-220AB



	D2

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
Е	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØΡ	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

 $^{^{\}star}$ M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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